



K. Memory (Design & Process Technology) 분과

2019년 2월 15일(금), 11:00-12:30

Room A (아라홀, 2층)

[FA2-K] Resistive Memory II

좌장: 김경민 교수(KAIST), 이재구 수석(삼성전자)

<p>FA2-K-1 11:00-11:15</p>	<p>SPICE Compact Model of the IGZO Memristor Considering both the Metal Electrode and the Process Sequence of the Deposition of Metal and IGZO Film Jun Tae Jang, Jungi Min, Donguk Kim, Jingyu Park, Sung-Jin Choi, Dong Myong Kim, and Dae Hwan Kim <i>School of Electrical Engineering., Kookmin University</i></p>
<p>FA2-K-2 11:15-11:30</p>	<p>Demonstration of both the Digital and Analog Memory Operations of the IGZO Resistive-Switching Devices by A Control of Metal Electrode/IGZO Combination Jungi Min, Jun Tae Jang, Donguk Kim, Jingyu Park, Sung-Jin Choi, Dong Myong Kim, and Dae Hwan Kim <i>School of Electrical Engineering, Kookmin University</i></p>
<p>FA2-K-3 11:30-11:45</p>	<p>Inorganically Connected NiO Nanocrystal for Flexible Resistive Memory(ReRAM) Hye-Won Yun^{1,2}, Haneun Kim², Soo-Jung Kim², SoongJu Oh², and Sung-Hoon Hong¹ ¹<i>ICT Materials Research Group, ETRI,</i> ²<i>Department of Materials Science and Engineering, Korea University</i></p>
<p>FA2-K-4 11:45-12:00</p>	<p>Flexible Resistive Switching Memory Devices based on Solution-Processed Metal-Oxide Dielectric Films Fabricated at Low Temperature Byoung-Soo Yu, Sang-Joon Park, and Tae-Jun Ha <i>Department of Electronic Materials Engineering, Kwangwoon University</i></p>
<p>FA2-K-5 12:00-12:15</p>	<p>A Study on Resistive Random Access Memory(ReRAM) based on Cross-Linked PVA Doped with Reduced Graphene Oxides(RGOs) Jinheon Jeong, Seung Yeob Kim, Kim Yeong Eun, and Sung Hun Jin <i>Department of Electronic Engineering, Incheon National University</i></p>
<p>FA2-K-6 12:15-12:30</p>	<p>Effects of Cu Dopant on Bipolar Resistive Switching in Oxygenated Amorphous Carbon Layer Da Seul Hyeon, Gabriel Jang, Taeyoon Kim, and Jinpyo Hong <i>Novel Functional Materials and Devices Lab, Department of Physics, Hanyang University</i></p>